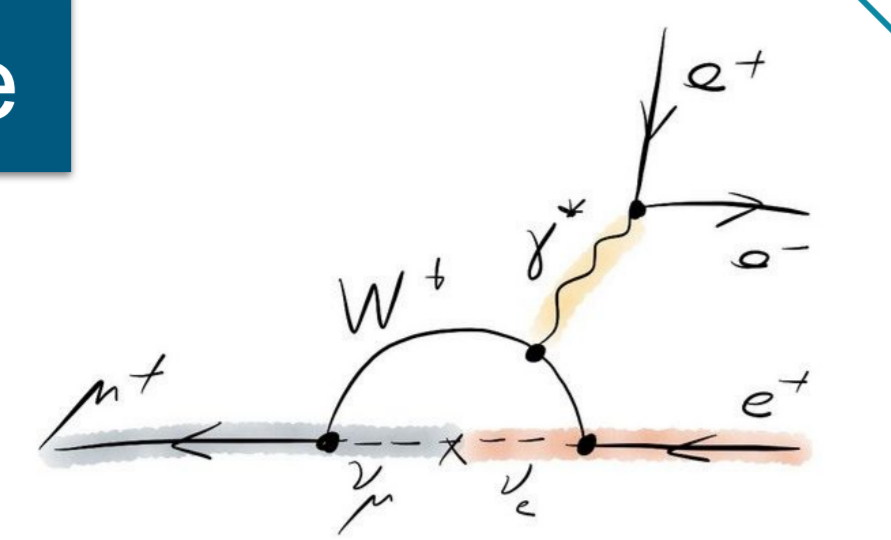
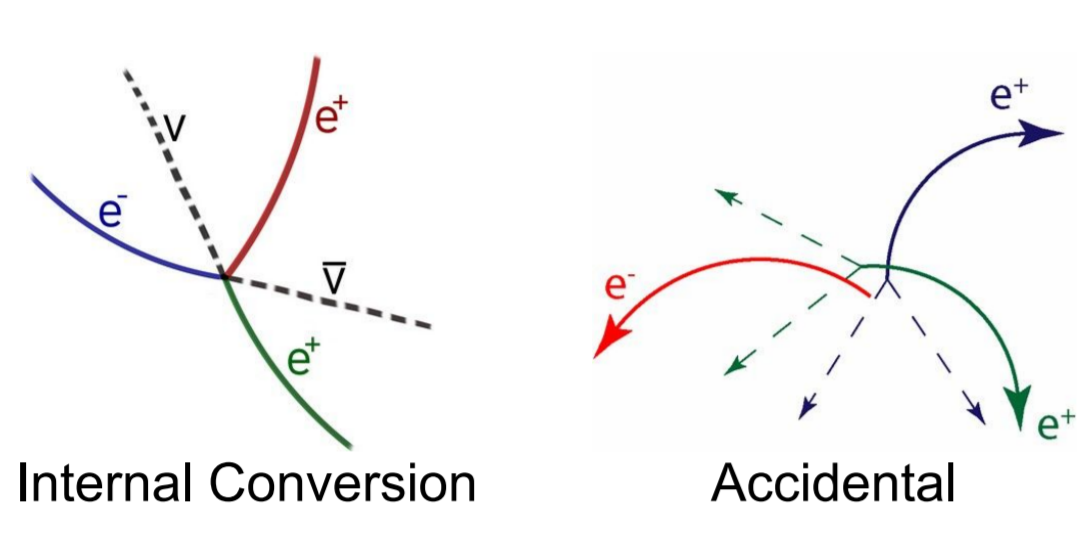




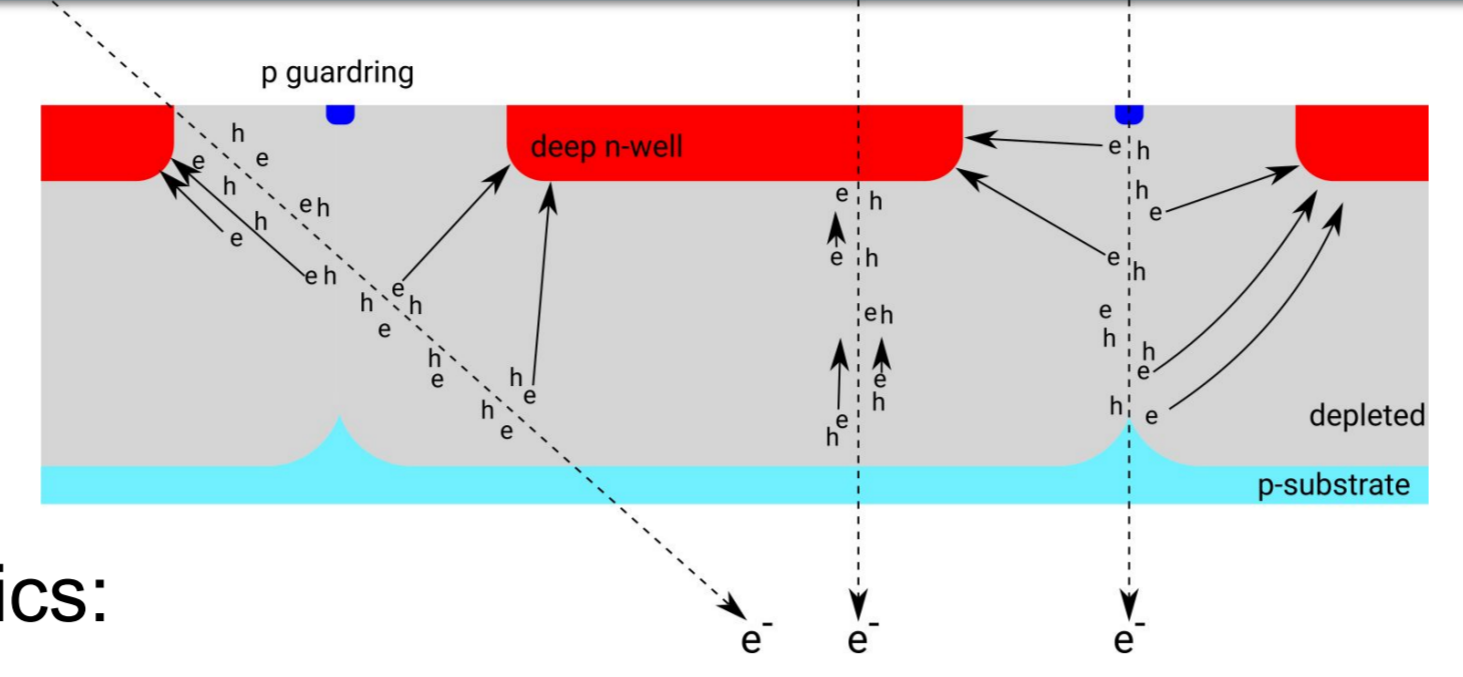
### Mu3e



- Search for the cIFV decay  
→  $\mu^+ \rightarrow e^+ e^- e^+ (\nu_{SM}: BR < 10^{-54})$
- Current limit (SINDRUM 1980):  
→  $BR < 10^{-12}$  @ 90 % CL
- Sensitivity Goal (Phase I):  
→ 1 in  $10^{15}$  decays
- High intensity  $\mu^+$  - beam  
→ Up to  $10^8$  decays / second
- Background suppression below sensitivity level

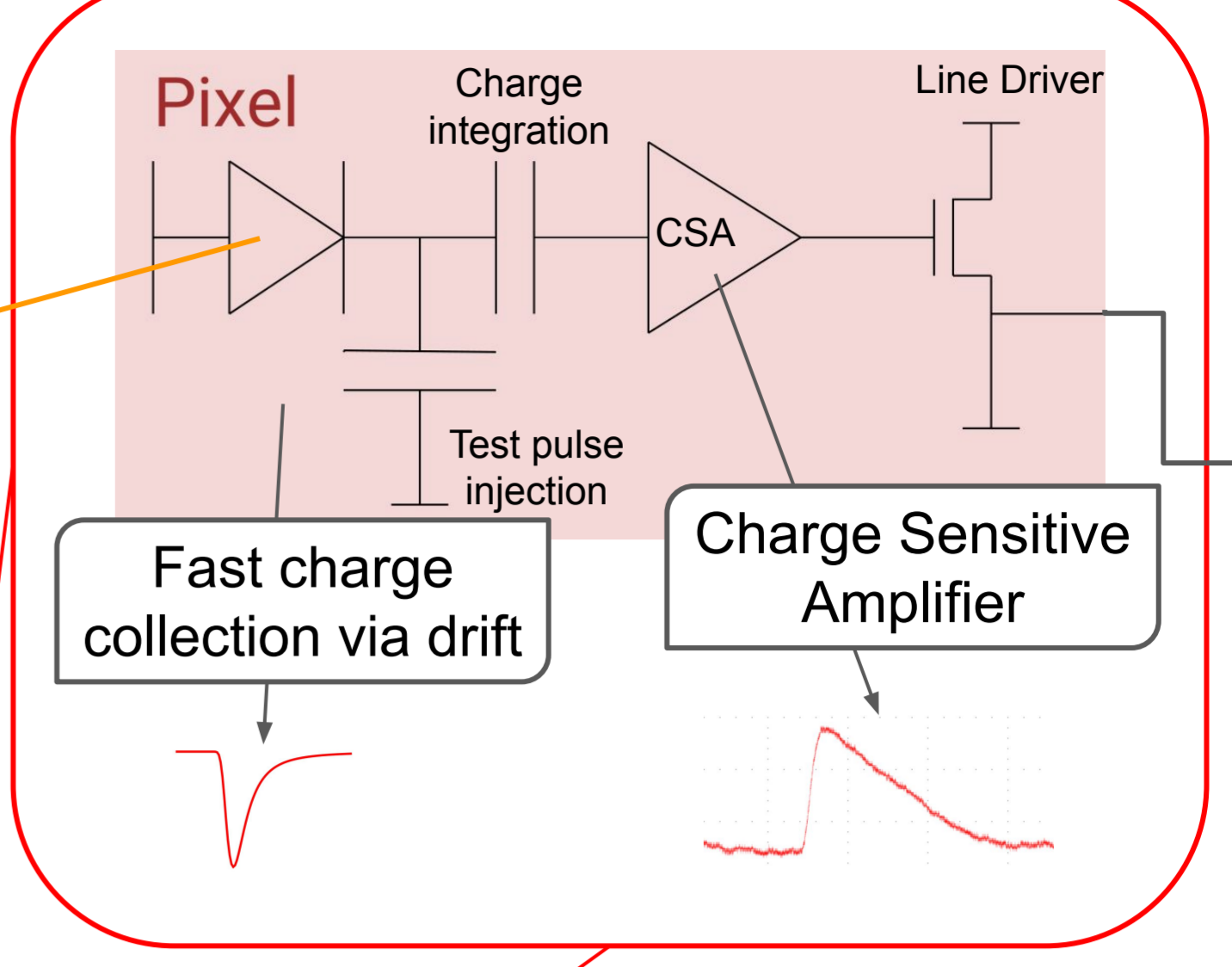


### High-Voltage Monolithic Active Pixel Sensor



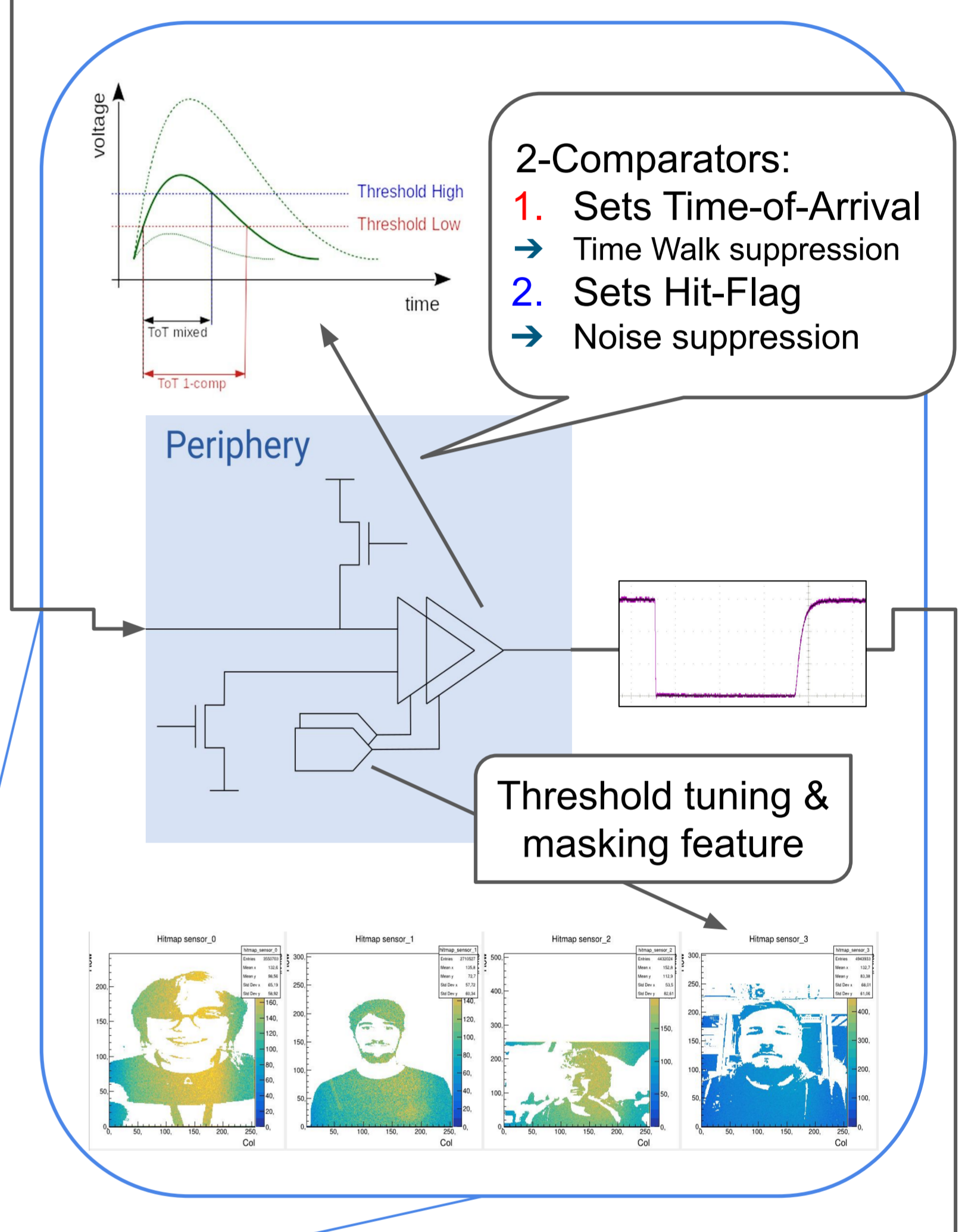
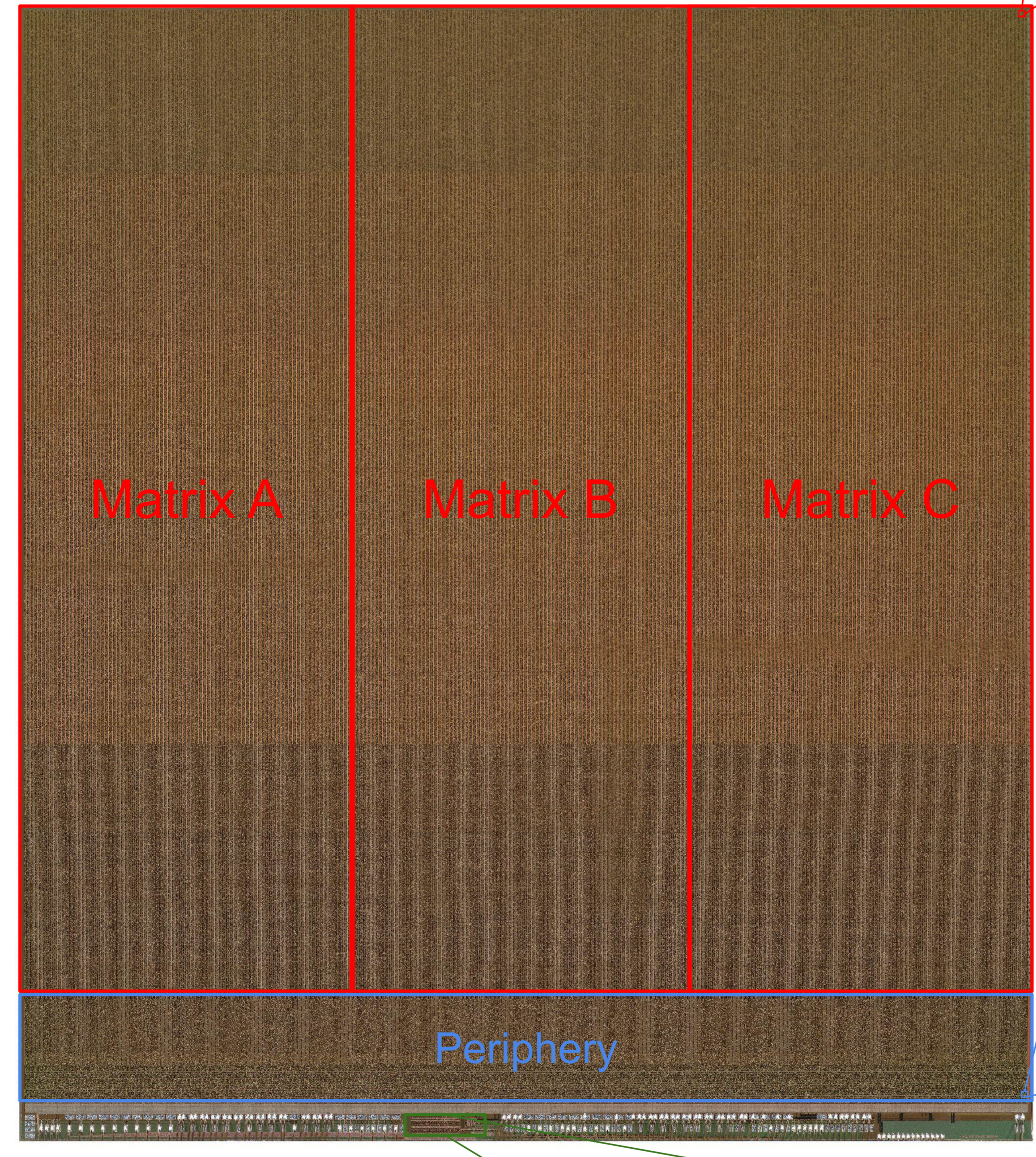
Characteristics:

- 180 nm HV-CMOS process (TSI Semiconductors) up to -120 V
- Low-ohmic substrate (10 - 400  $\Omega\text{cm}$ )
- Diode: deep n-well reversed biased (~10 - 30  $\mu\text{m}$  depletion)
- Chips can be thinned down to 50  $\mu\text{m}$



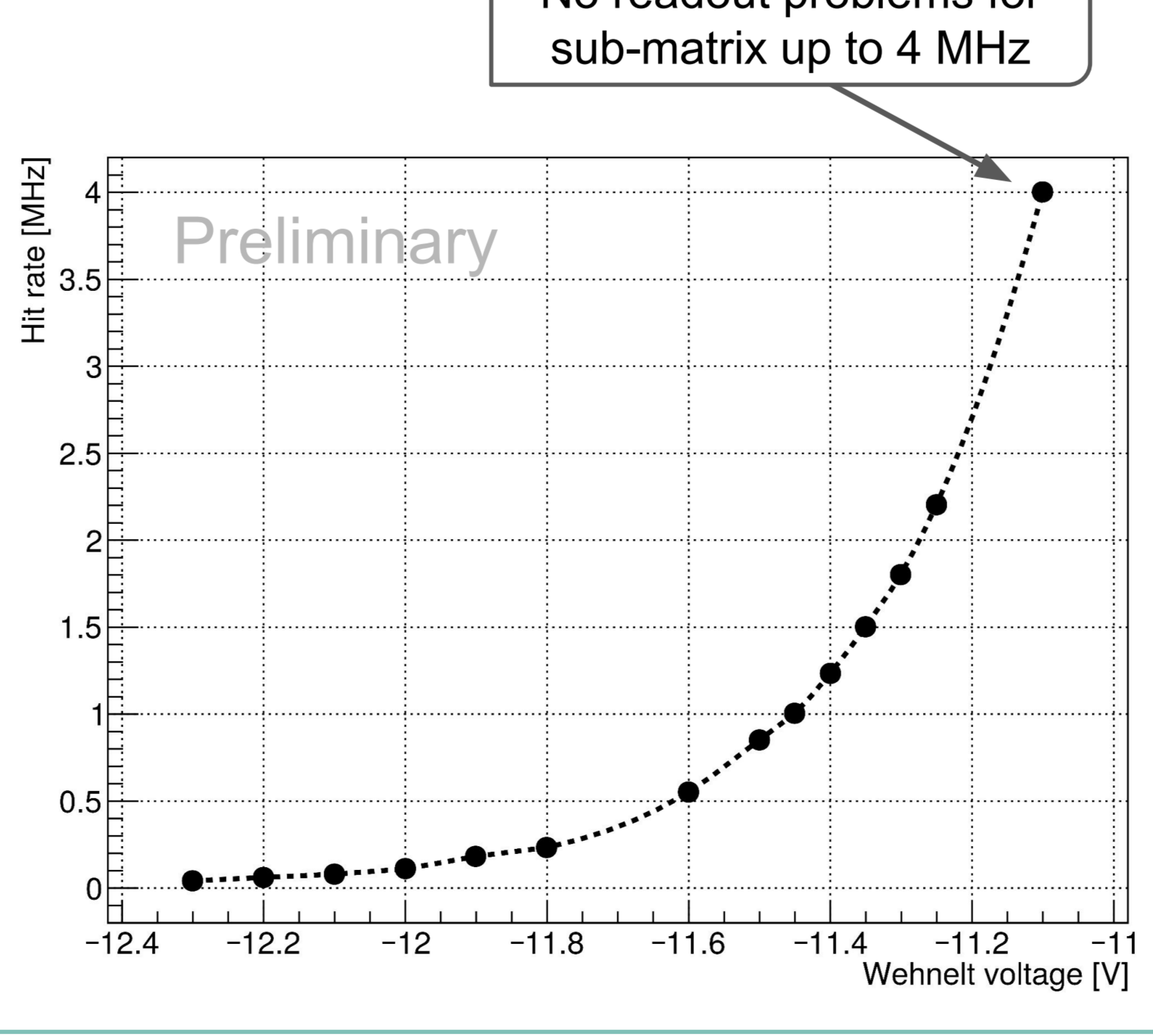
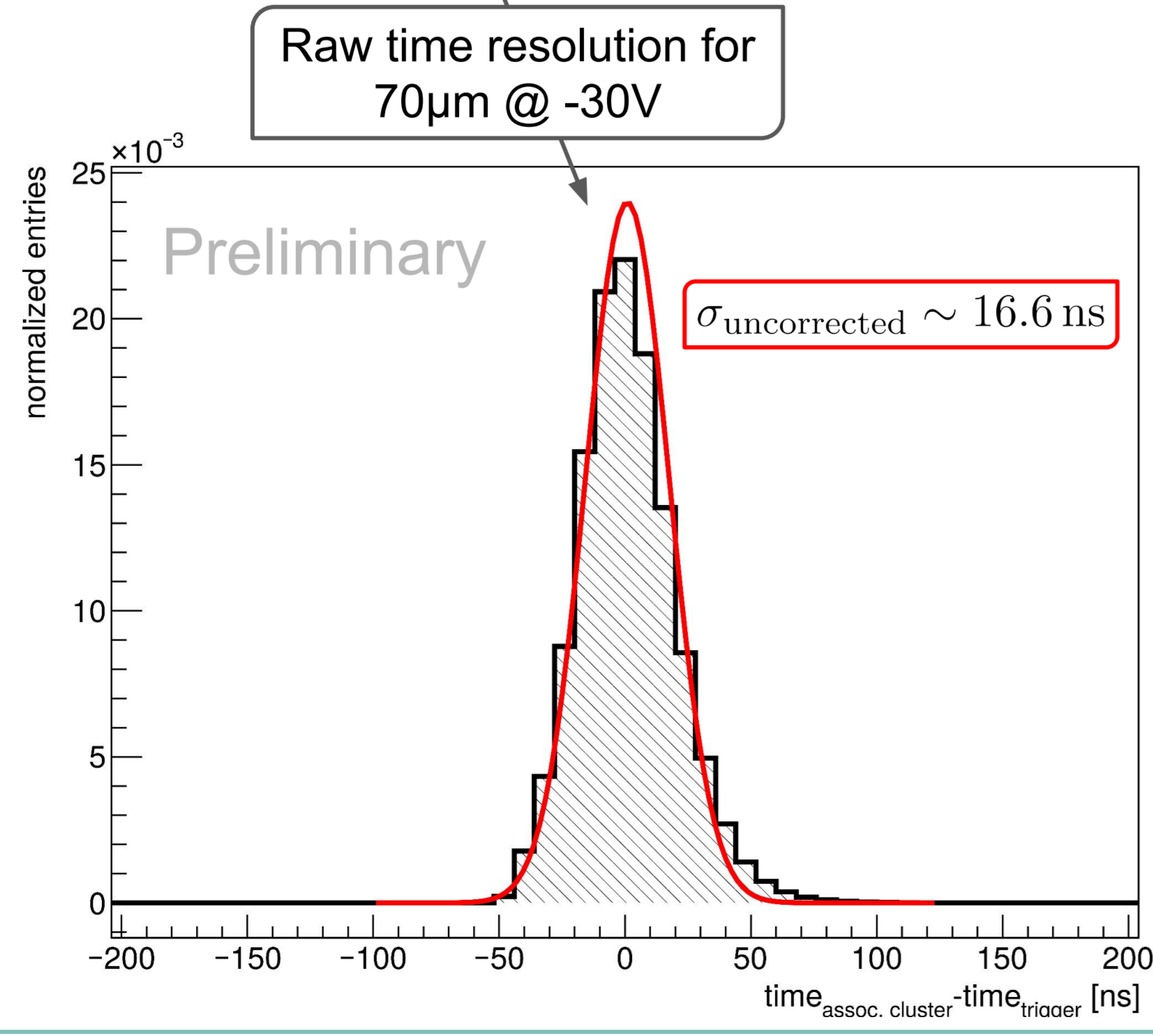
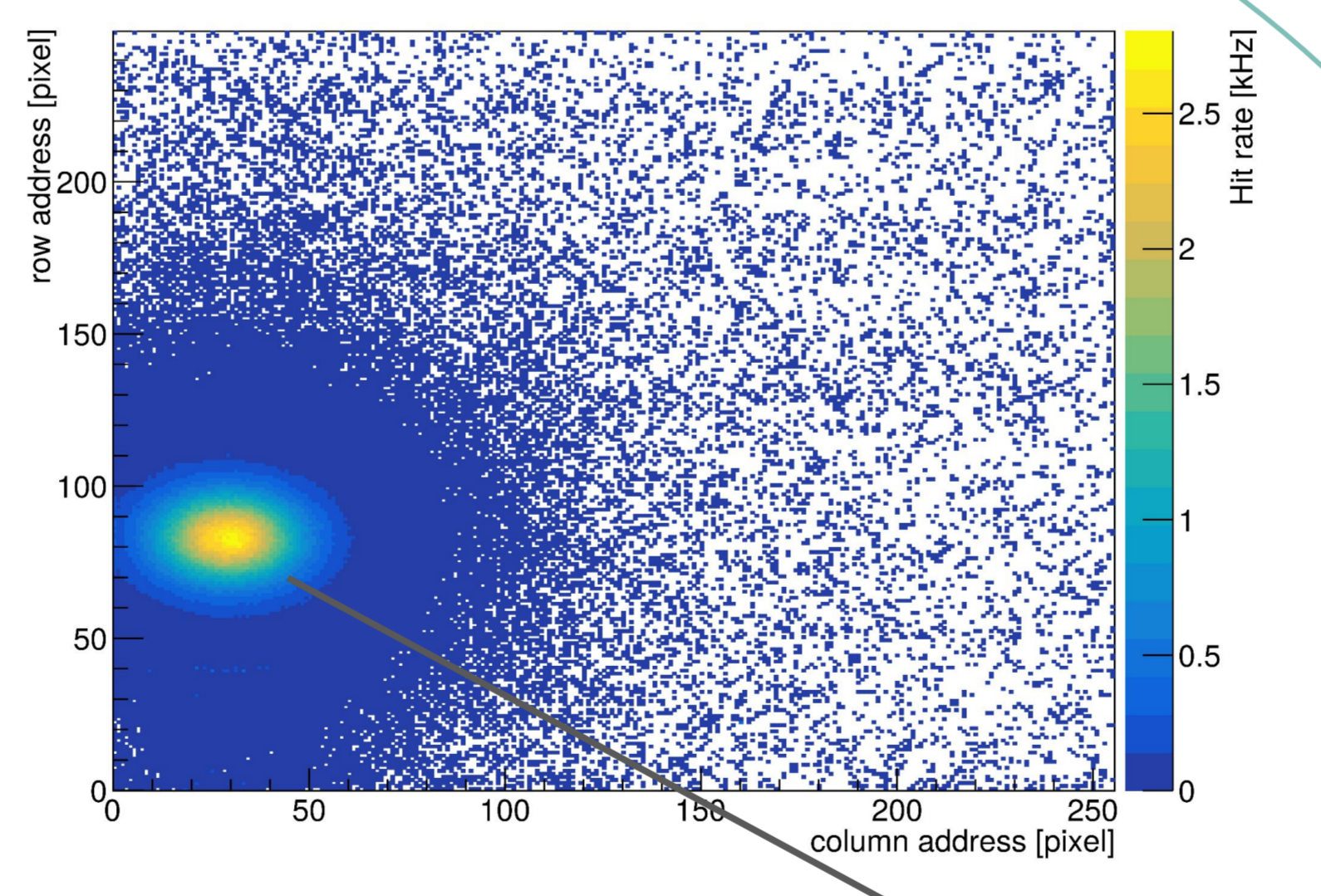
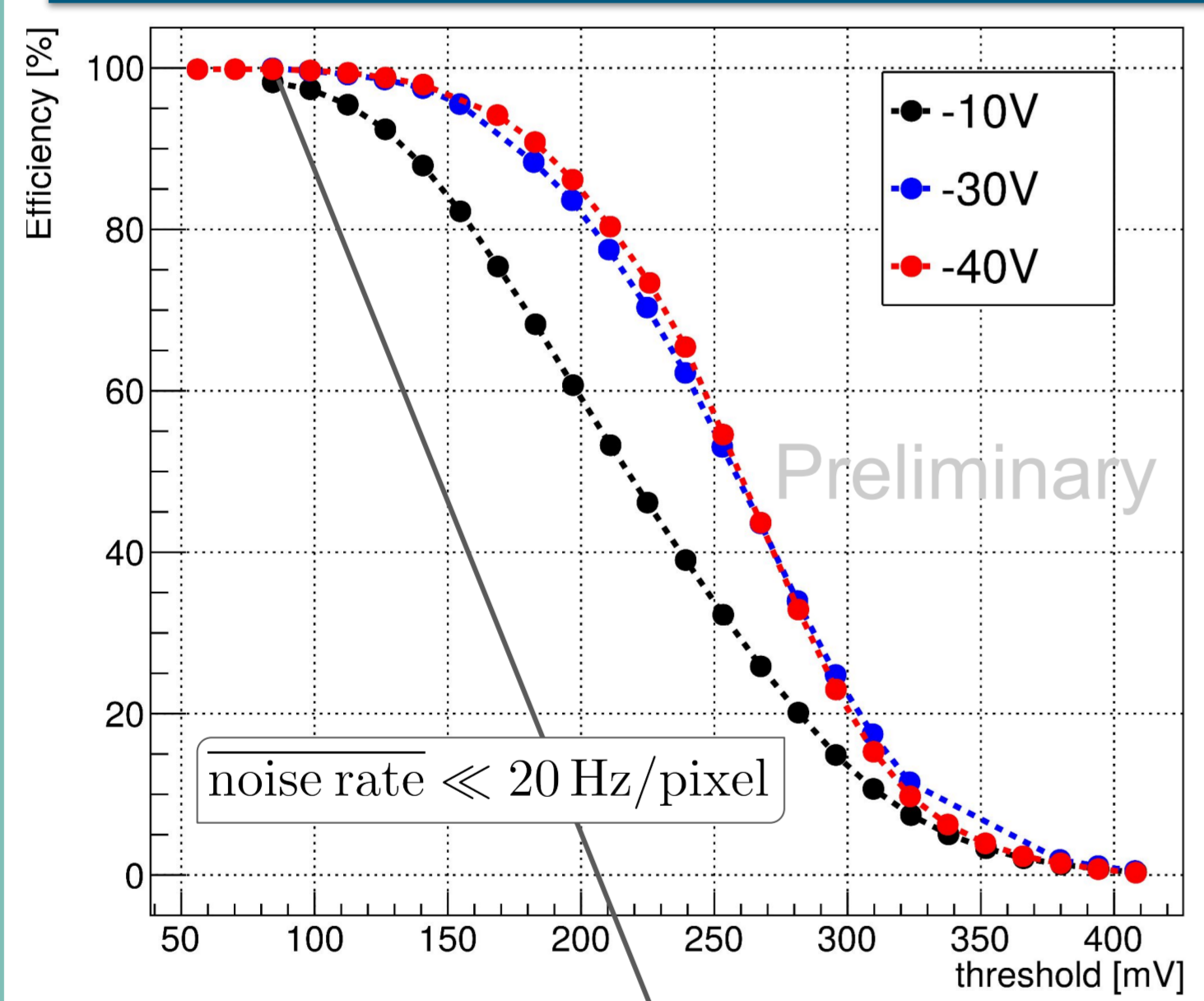
Up to ~2.2 cm line cross talk suppressing routing on 3 aluminium metal layers per pixel !

Pixel size [ $\mu\text{m}^2$ ]	80 x 80
Pixel matrix	256 x 250
Active area [ $\text{mm}^2$ ]	20.48 x 20.0
Sensor size [ $\text{mm}^2$ ]	20.66 x 23.18
Thickness [ $\mu\text{m}$ ]	50, 70
Radiation length [ $x/X_0$ ]	~ 0.5‰, ~ 0.7‰
Resistivity [ $\Omega\text{cm}$ ]	80, 370
ToA + ToT [bits]	11 + 5
TS binning [ns]	8 (option for 1.6)
Data links	3 + 1 (mux)
Link speed [Gbit/s]	1.25

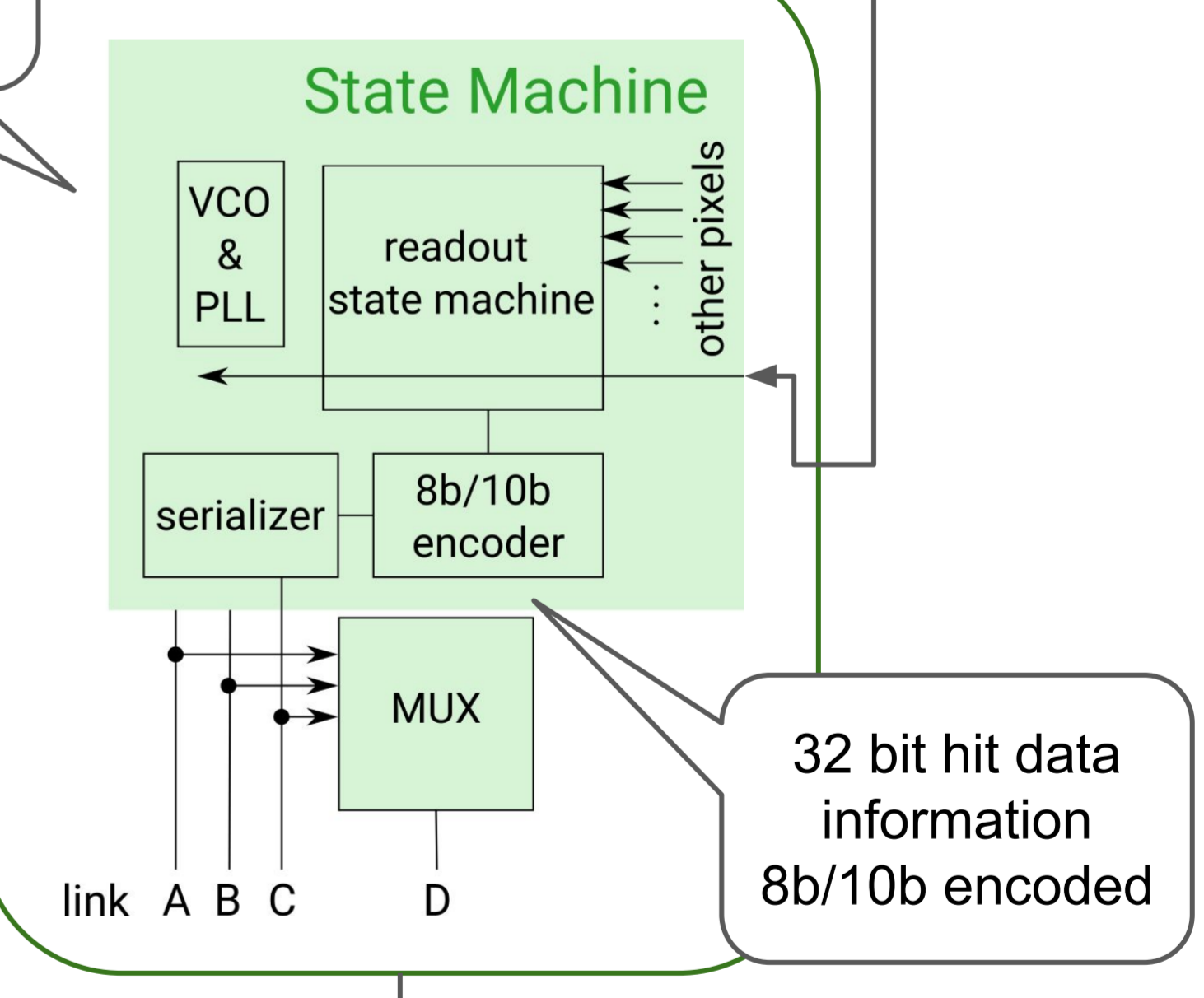


Column-drain readout managed by readout state machine!

### MuPix 11 - 70 $\mu\text{m}$ - Performance Study

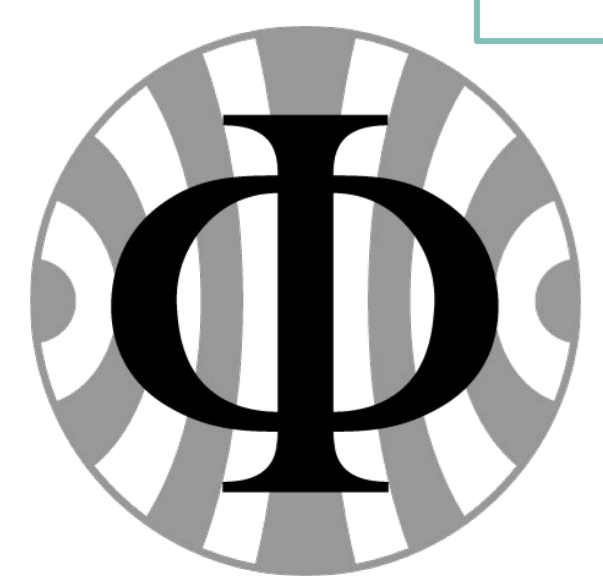


One readout state machine per sub-matrix!



32 bit hit data information 8b/10b encoded

1.25 Gbit/s data links with zero suppression



by David M. Immig<sup>1</sup>  
for the Mu3e Collaboration

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